for actual use of this tabulation, please refer to:
A. Vasilescu and G. Lindstroem
Displacement damage in Silicon
on-line compilation: http://sesam.desy.de/~gunnar/Si-dfuncs

electron induced displacement damage in silicon
listed for kinetic energies between 300 keV and 200 MeV:
The only reliable data are from:
G.P.Summers et al., IEEE NS 40, No 6 (1993), 1372

Ekin [MeV]	D/95MeVmb
3,000E-01	3,182E-03
5,000E-01	7,998E-03
7,000E-01	1,139E-02
1,000E+00	1,543E-02
2,000E+00	2,489E-02
3,000E+00	3,126E-02
5,000E+00	3,979E-02
7,000E+00	4,558E-02
1,000E+01	5,160E-02
2,000E+01	6,241E-02
3,000E+01	6,780E-02
5,000E+01	7,344E-02
7,000E+01	7,634E-02
1,000E+02	7,870E-02
2,000E+02	8,106E-02